DEPOSITED FILM FORMATION METHOD UTILIZING SELECTIVE DEPOSITION BY USE OF ALKYL ALUMINUM HYDRIDE

ABSTRACT OF THE DISCLOSURE

By providing a deposited film formation method in which aluminum or a metal composed mainly of aluminum of good quality is selectively deposited according to the CVD method utilizing an alkyl aluminum hydride and hydrogen, and then pure aluminum or a metal composed mainly of aluminum is non-selectively deposited, it becomes possible to form an electro-conductive film of good quality within fine openings or on an insulating layer.

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